

RJH60D2DPP-E0

600V - 12A - IGBT

Application: Inverter

R07DS0894EJ0100

Rev.1.00

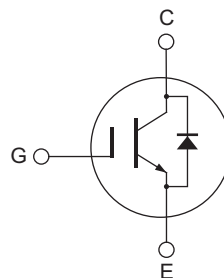
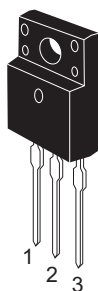
Nov 01, 2012

Features

- Short circuit withstand time (5 μ s typ.)
- Low collector to emitter saturation voltage
 $V_{CE(sat)} = 1.7$ V typ. (at $I_C = 12$ A, $V_{GE} = 15$ V, $T_a = 25^\circ\text{C}$)
- Built in fast recovery diode (100 ns typ.) in one package
- Trench gate and thin wafer technology
- High speed switching
 $t_f = 80$ ns typ. (at $V_{CC} = 300$ V, $V_{GE} = 15$ V, $I_C = 12$ A, $R_g = 5$ Ω , $T_a = 25^\circ\text{C}$, inductive load)

Outline

RENESAS Package code: PRSS0003AG-A
(Package name: TO-220FP)



1. Gate
2. Collector
3. Emitter

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item		Symbol	Ratings	Unit
Collector to emitter voltage / diode reverse voltage		V_{CES} / V_R	600	V
Gate to emitter voltage		V_{GES}	± 30	V
Collector current	$T_c = 25^\circ\text{C}$	I_C	25	A
	$T_c = 100^\circ\text{C}$	I_C	12	A
Collector peak current		$i_{c(peak)}$ ^{Note1}	50	A
Collector to emitter diode forward current		i_{DF}	12	A
Collector to emitter diode forward peak current		$i_{DF(peak)}$ ^{Note1}	50	A
Collector dissipation		P_C ^{Note2}	34	W
Junction to case thermal resistance (IGBT)		θ_{j-c} ^{Note2}	3.7	$^\circ\text{C/W}$
Junction to case thermal resistance (Diode)		θ_{j-cd} ^{Note2}	4.9	$^\circ\text{C/W}$
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature		T_{stg}	-55 to +150	$^\circ\text{C}$

Notes: 1. $PW \leq 10$ μ s, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ\text{C}$

Electrical Characteristics

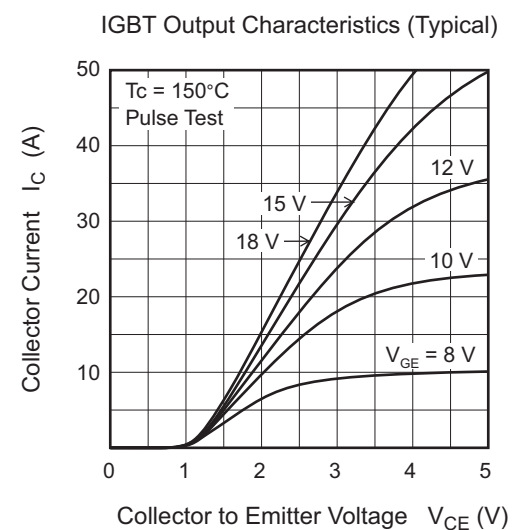
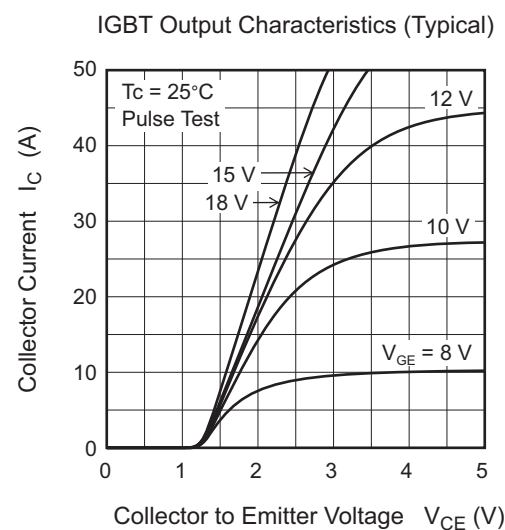
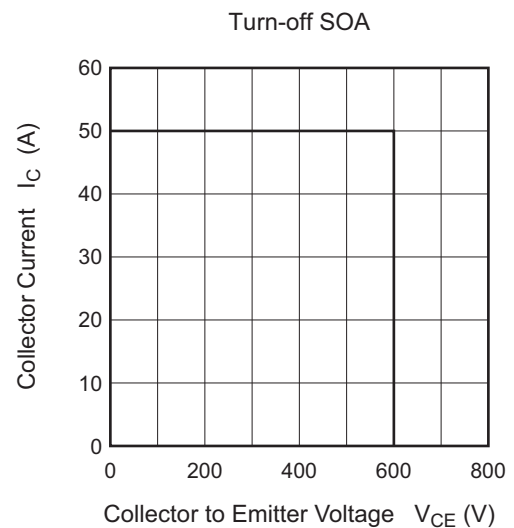
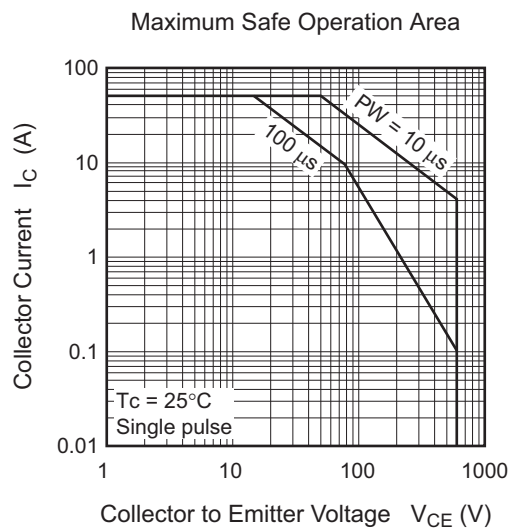
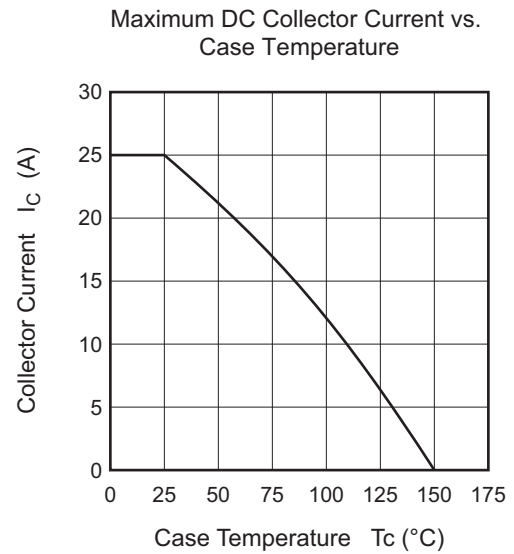
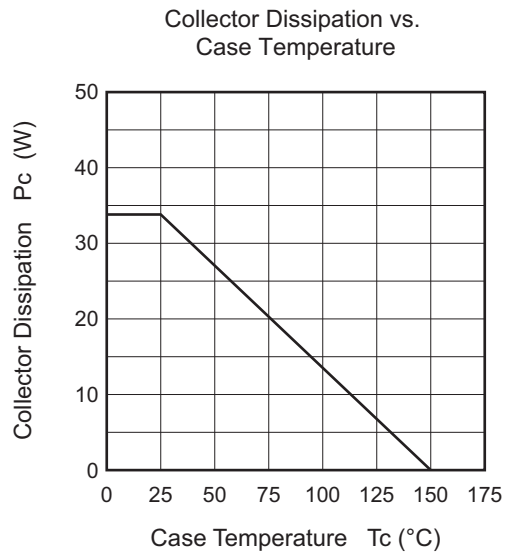
(Ta = 25°C)

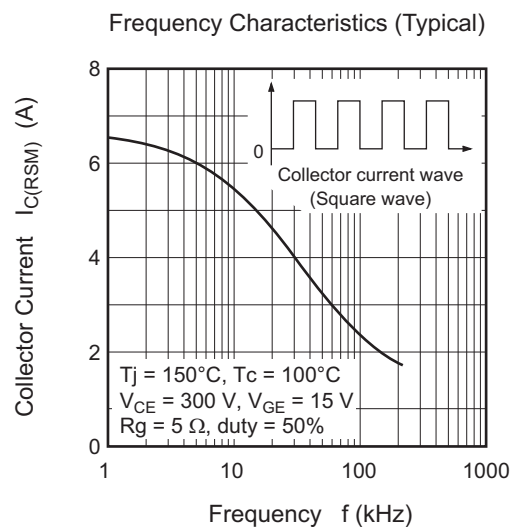
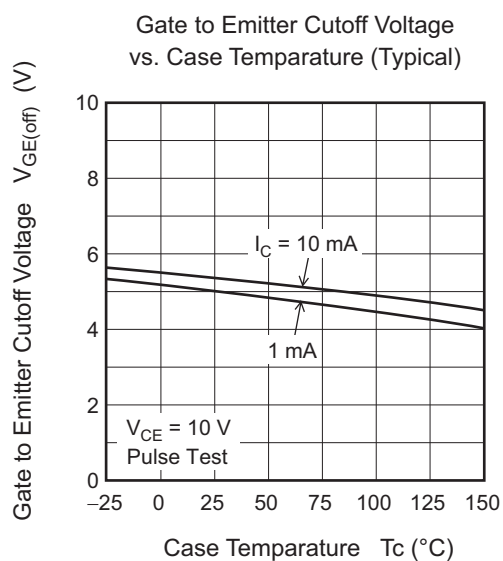
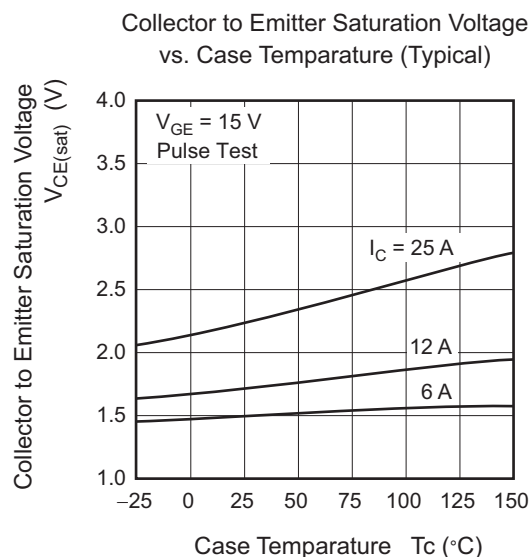
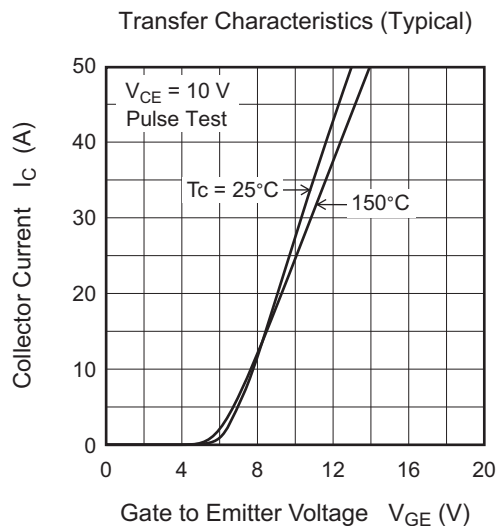
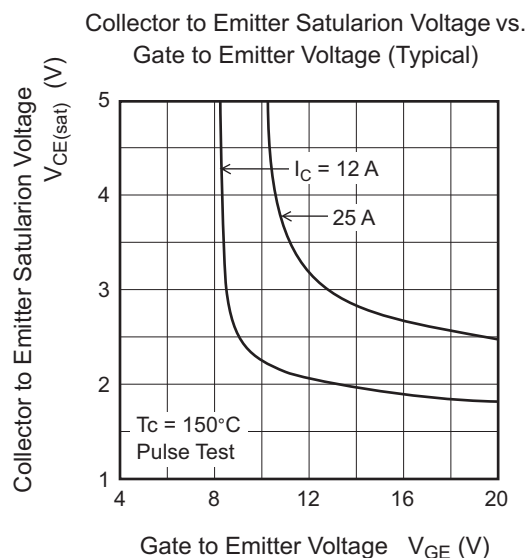
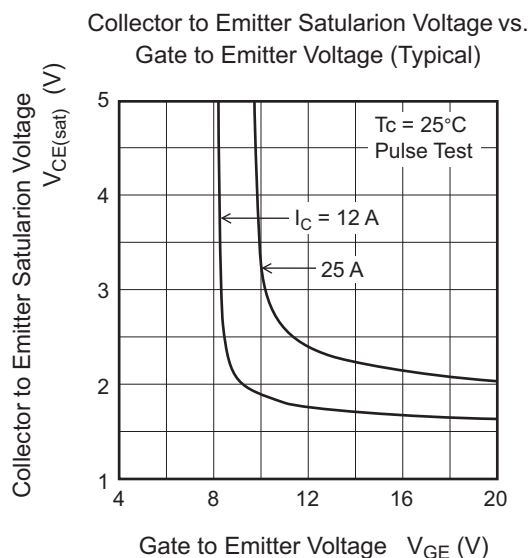
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to emitter breakdown voltage	$V_{BR(CES)}$	600	—	—	V	$I_C = 10 \mu A, V_{GE} = 0$
Zero gate voltage collector current / Diode reverse current	I_{CES} / I_R	—	—	5	μA	$V_{CE} = 600 V, V_{GE} = 0$
Gate to emitter leak current	I_{GES}	—	—	± 1	μA	$V_{GE} = \pm 30 V, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(off)}$	4.0	—	6.0	V	$V_{CE} = 10 V, I_C = 1 mA$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	1.7	2.2	V	$I_C = 12 A, V_{GE} = 15 V$ ^{Note3}
	$V_{CE(sat)}$	—	2.2	—	V	$I_C = 25 A, V_{GE} = 15 V$ ^{Note3}
Input capacitance	C_{ies}	—	430	—	pF	$V_{CE} = 25 V$
Output capacitance	C_{oes}	—	40	—	pF	$V_{GE} = 0$
Reveres transfer capacitance	C_{res}	—	12	—	pF	$f = 1 MHz$
Total gate charge	Q_g	—	19	—	nC	$V_{GE} = 15 V$
Gate to emitter charge	Q_{ge}	—	4	—	nC	$V_{CE} = 300 V$
Gate to collector charge	Q_{gc}	—	7	—	nC	$I_C = 12 A$
Turn-on delay time	$t_{d(on)}$	—	32	—	ns	$V_{CC} = 300 V$
Rise time	t_r	—	13	—	ns	$V_{GE} = 15 V$
Turn-off delay time	$t_{d(off)}$	—	85	—	ns	$I_C = 12 A$
Fall time	t_f	—	80	—	ns	$R_g = 5 \Omega$
Turn-on energy	E_{on}	—	0.10	—	mJ	Inductive load
Turn-off energy	E_{off}	—	0.16	—	mJ	
Total switching energy	E_{total}	—	0.26	—	mJ	
Short circuit withstand time	t_{sc}	3.0	5.0	—	μs	$V_{CC} \leq 360 V, V_{GE} = 15 V$

FRD Forward voltage	V_F	—	1.2	1.6	V	$I_F = 12 A$ ^{Note3}
FRD reverse recovery time	t_{rr}	—	100	—	ns	$I_F = 12 A$
FRD reverse recovery charge	Q_{rr}	—	0.2	—	μC	$di_F/dt = 100 A/\mu s$
FRD peak reverse recovery current	I_{rr}	—	5.0	—	A	

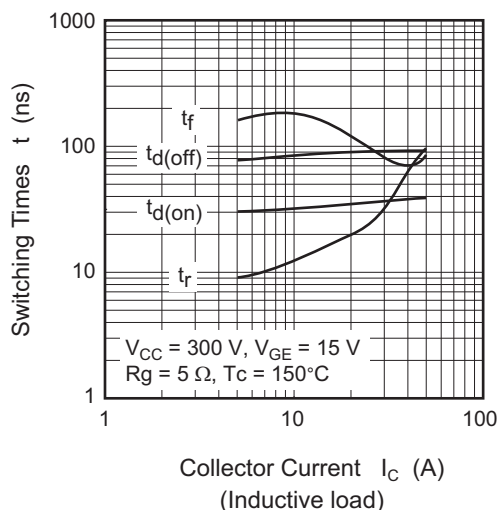
Notes: 3. Pulse test.

Main Characteristics

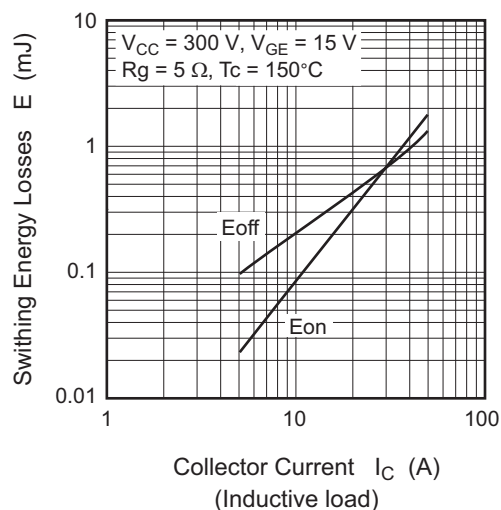




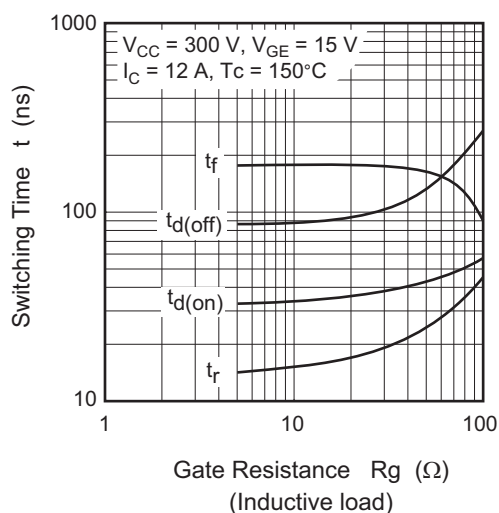
Switching Characteristics (Typical) (1)



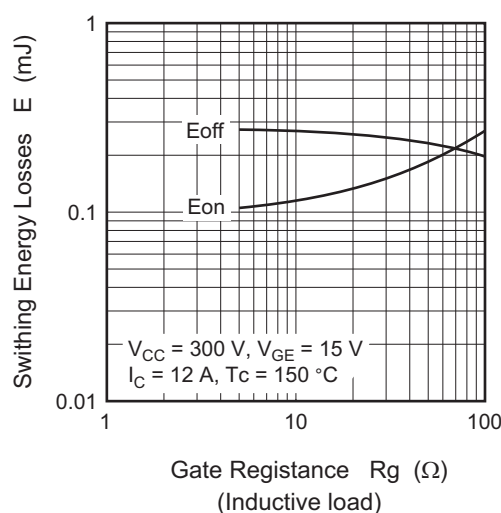
Switching Characteristics (Typical) (2)



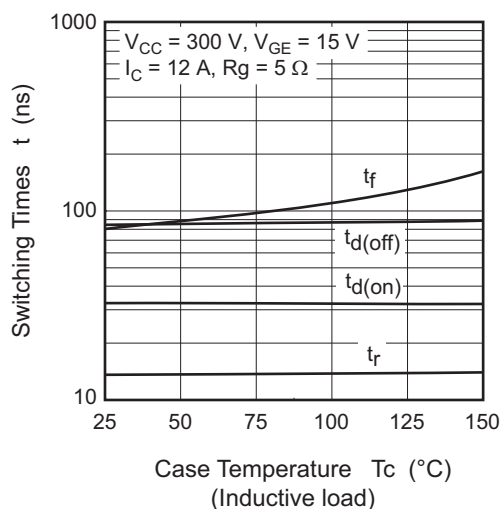
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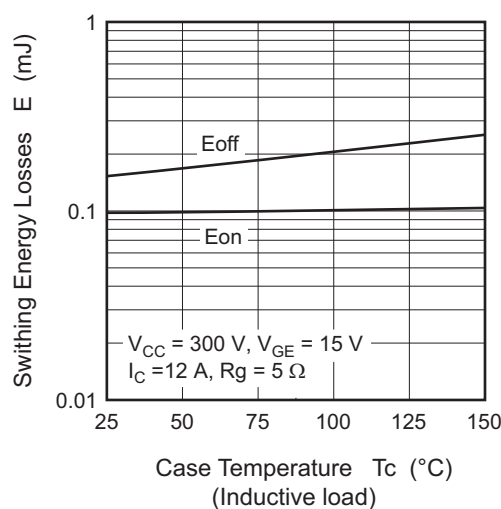
Switching Characteristics (Typical) (4)

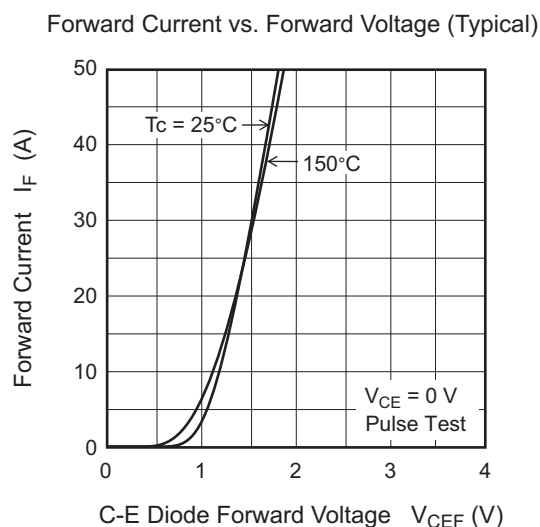
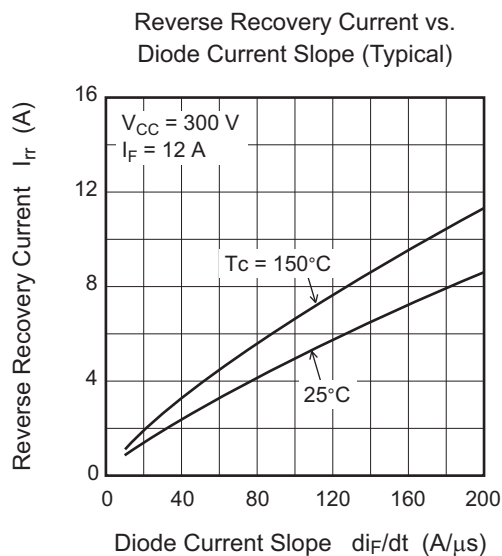
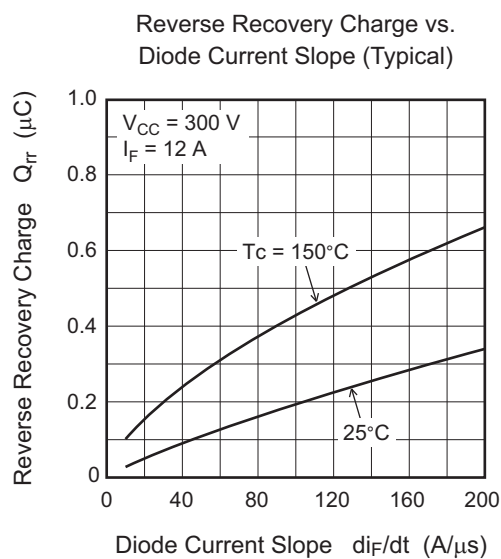
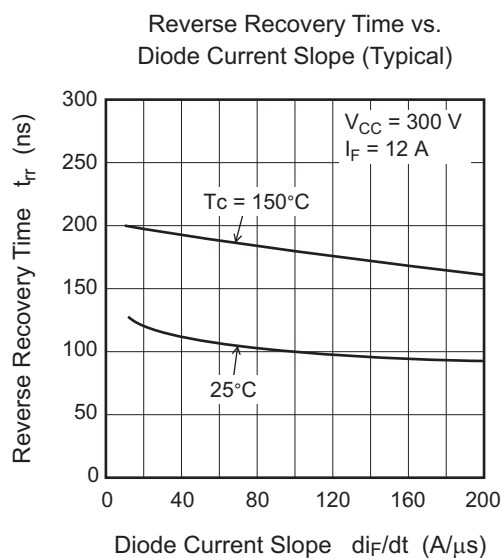
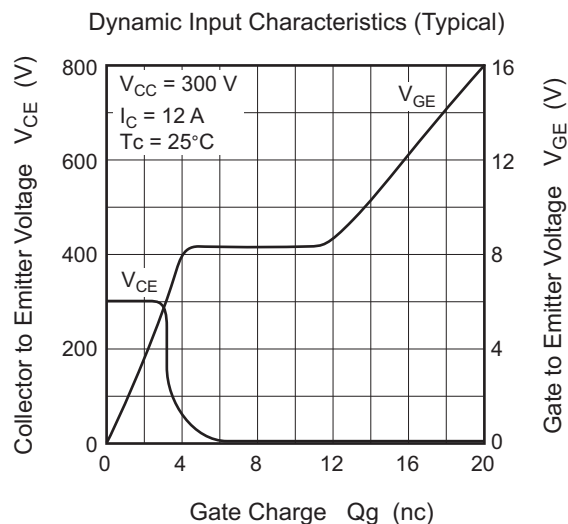
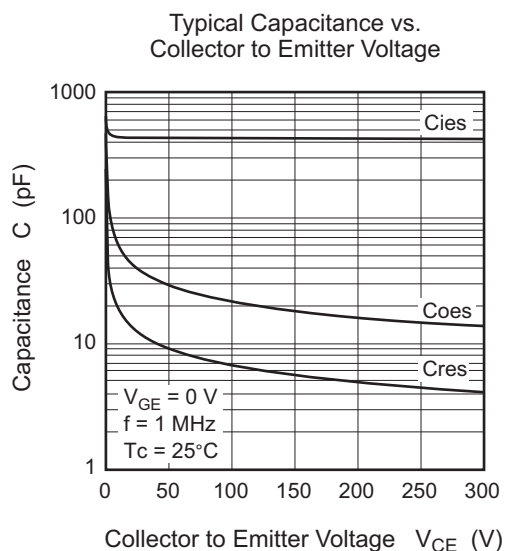


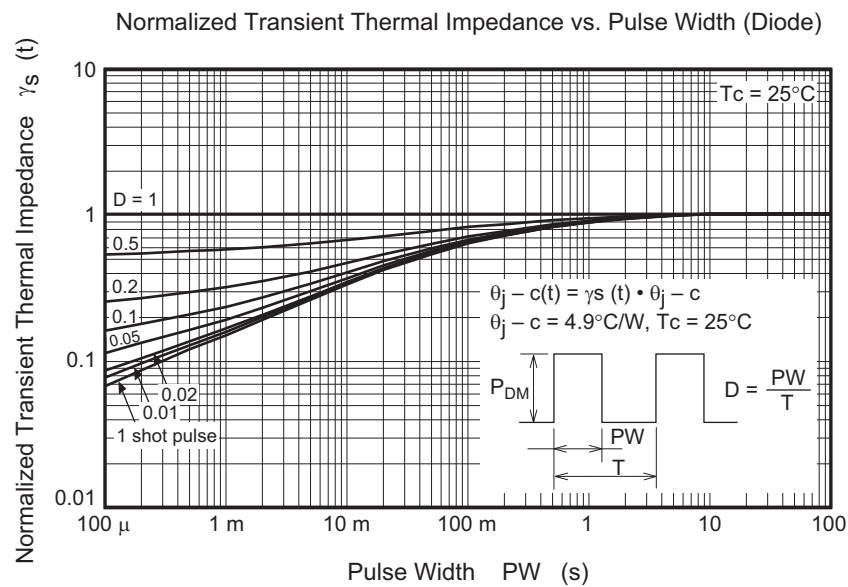
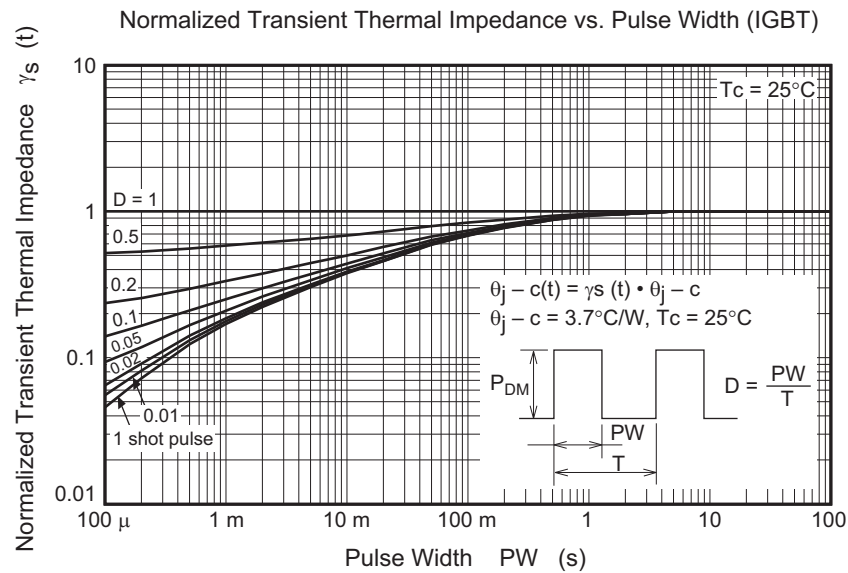
Switching Characteristics (Typical) (5)



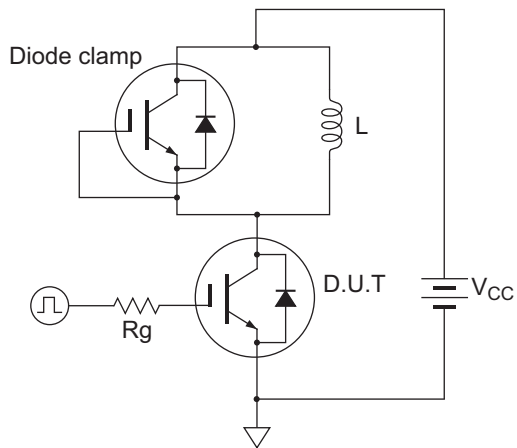
Switching Characteristics (Typical) (6)



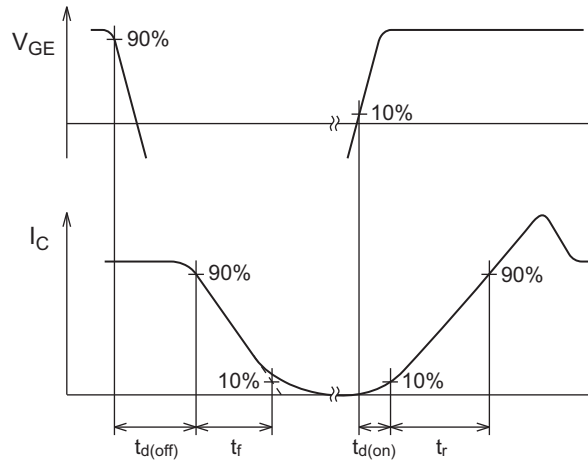




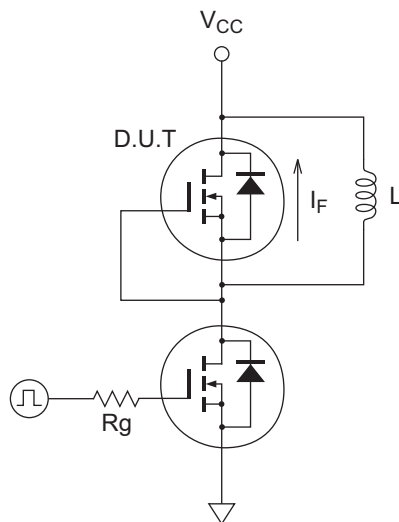
Switching Time Test Circuit



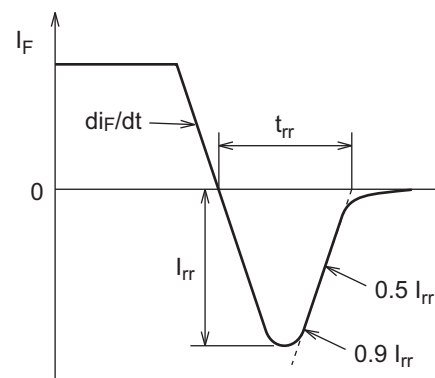
Waveform



Diode Reverse Recovery Time Test Circuit



Waveform



Package Dimension

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]	Unit: mm
TO-220FP	—	PRSS0003AG-A	—	1.9g	

Technical drawing of the RJH60D2DPP-E0 package showing dimensions in mm:

- Top View:**
 - Overall width: 10.16 ± 0.20
 - Overall height: 15.87 ± 0.20
 - Pin pitch: 3.18 ± 0.10
 - Pin width: 3.3 ± 0.2
 - Pin length: 12.98 ± 0.30
 - Pin diameter: 0.80 ± 0.20
 - Pin spacing: 5.08 ± 0.20
 - Pin length (Max): 1.47
 - Pin length (Typ): 1.28 ± 0.30
 - Pin length (Min): 0.50 (with $+0.10$ and -0.05 tolerances)
- Side View:**
 - Overall height: 6.68 ± 0.20
 - Pin length: 2.76 ± 0.20
 - Pin length (Max): 2.54 ± 0.20
- Bottom View:**
 - Overall width: 4.7 ± 0.2

Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJH60D2DPP-E0#T2	1000 pcs	Box (Tube)

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